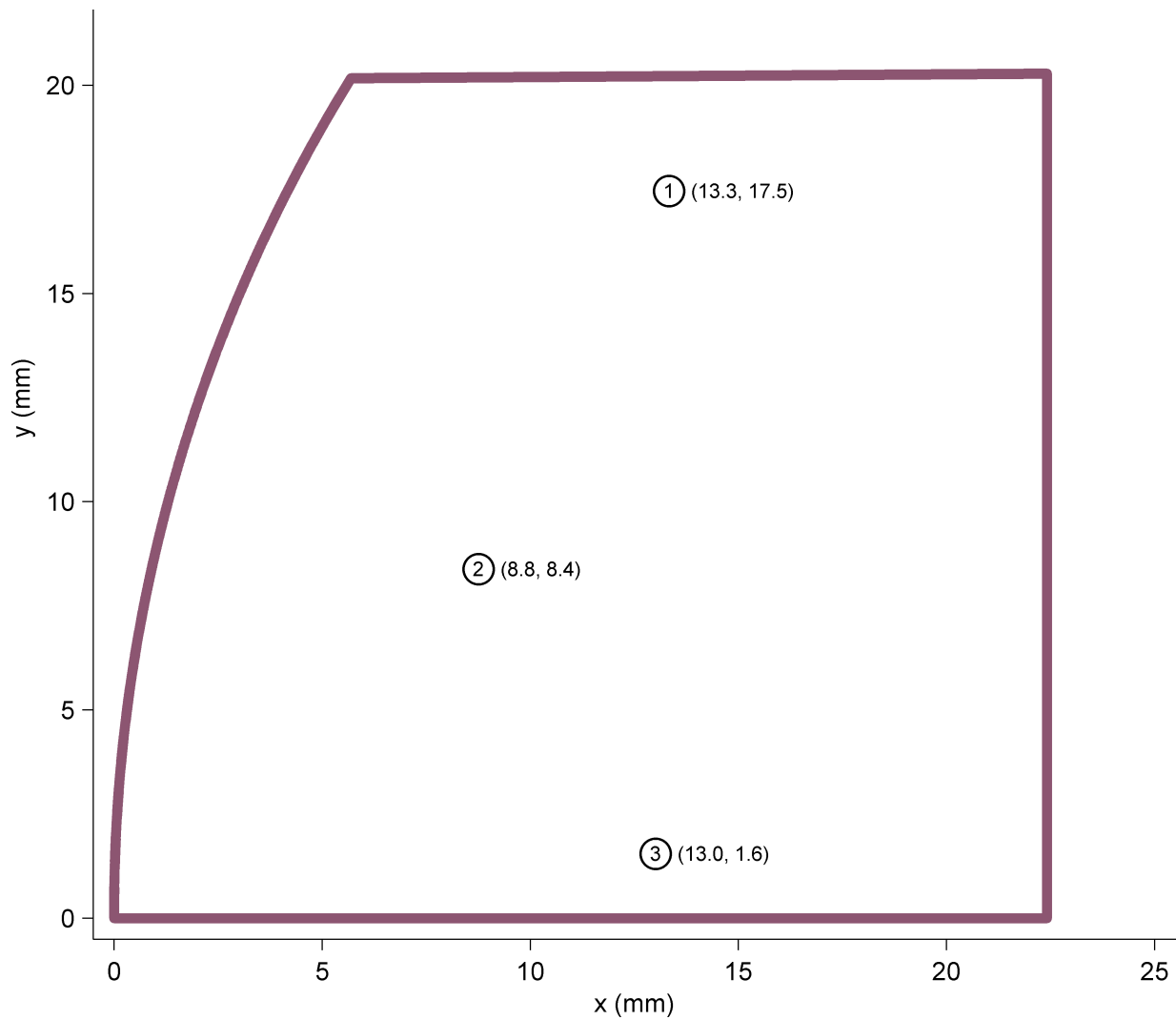


Sample S5515 Datasheet

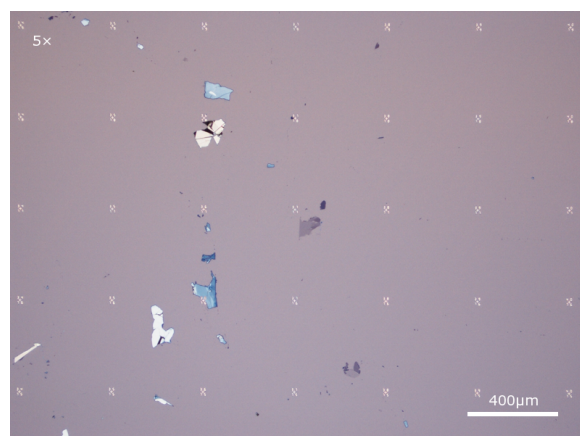
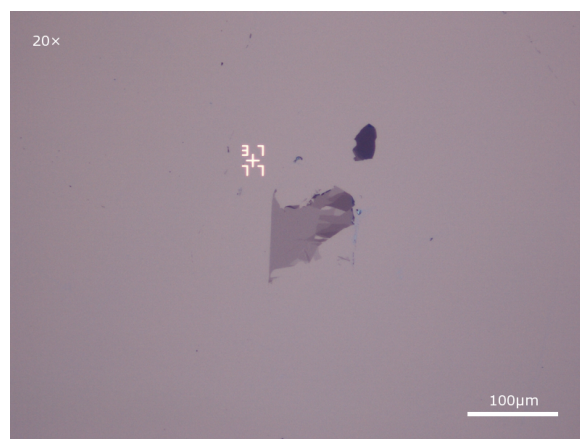
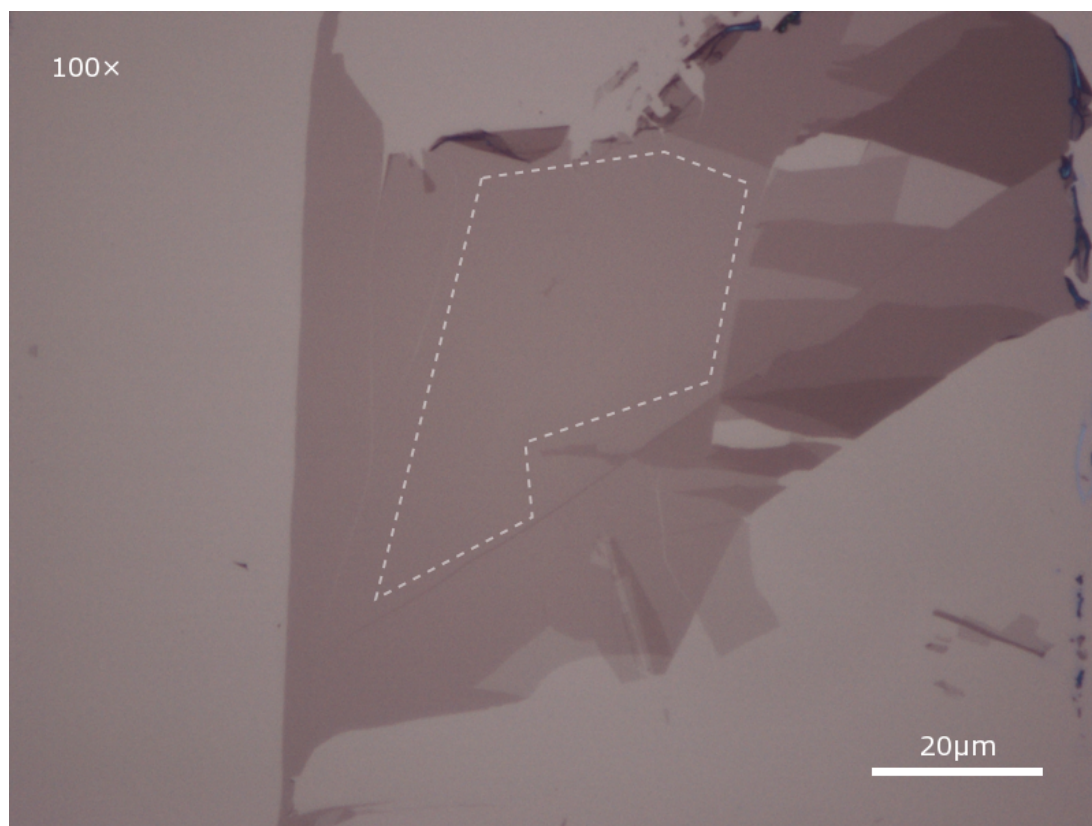
Parent Wafer

Supplier	IDB Technologies Ltd.
Diameter	100mm
Si Orientation	<100>
Si Thickness	525 μm
Si Doping	N-type, arsenic
Resistivity	0.001-0.010 Ωcm
Oxide	90 nm dry thermal oxide

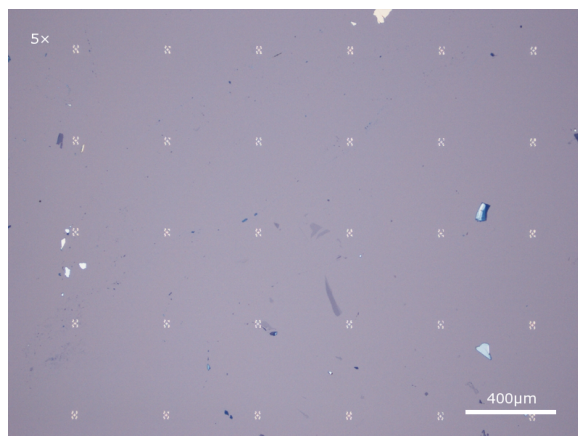
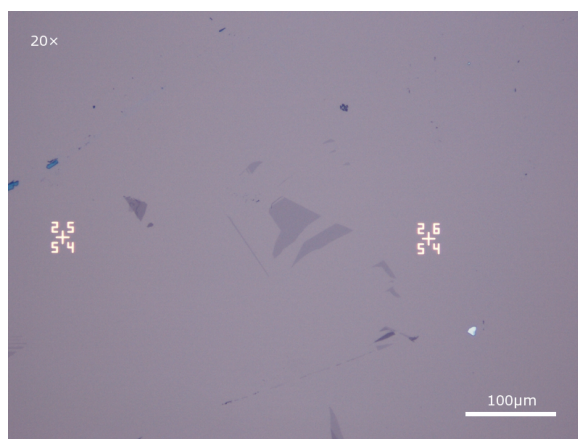
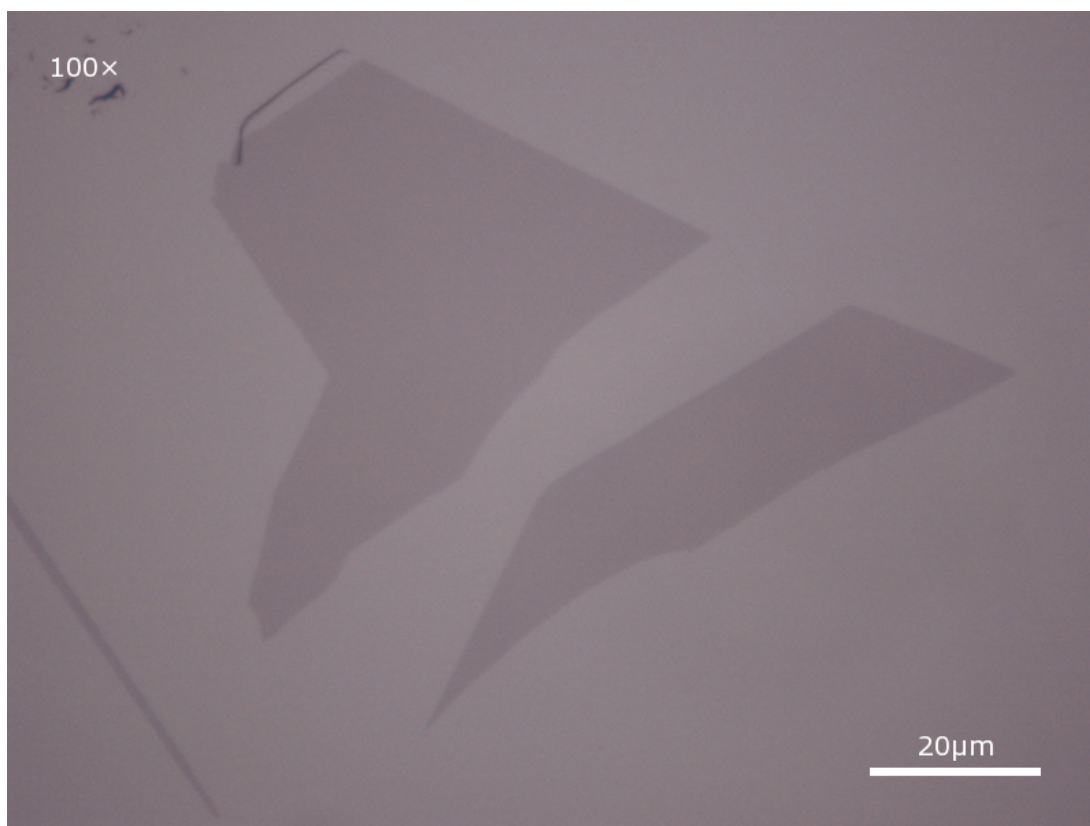
Substrate Map



**Flake 1 of 3: $x=13.3\text{mm}$, $y=17.5\text{mm}$, $>1000\text{ }\mu\text{m}^2$ bilayer region
(dashed perimeter)**



Flake 2 of 3: $x=8.8\text{mm}$, $y=8.4\text{mm}$, $>1500\text{ }\mu\text{m}^2$ and $>800\text{ }\mu\text{m}^2$ monolayer flakes



Flake 3 of 3: $x=13.0\text{mm}$, $y=1.6\text{mm}$, $>6000\text{ }\mu\text{m}^2$ and $>12000\text{ }\mu\text{m}^2$ monolayer flakes

